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ON Semiconductor N02L6181AB28I

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**ON Semiconductor®** 



### N02L6181A

### 2Mb Ultra-Low Power Asynchronous CMOS SRAM

128Kx16 bit

### Overview

The N02L6181A is an integrated memory device containing a 2 Mbit Static Random Access Memory organized as 131,072 words by 16 bits. The device is designed and fabricated using ON Semiconductor's advanced CMOS technology to provide both high-speed performance and ultra-low power. The base design is the same as ON Semiconductor's N02L63W3A, which is processed to operate at higher voltages. The device operates with a single chip enable ( $\overline{CE}$ ) control and output enable  $(\overline{OE})$  to allow for easy memory expansion. Byte controls ( $\overline{UB}$  and  $\overline{LB}$ ) allow the upper and lower bytes to be accessed independently. The N02L6181A is optimal for various applications where low-power is critical such as battery backup and hand-held devices. The device can operate

over a very wide temperature range of -40°C to

+85°C and is available in JEDEC standard packages compatible with other standard 128Kb x 16 SRAMs. **Product Family** 

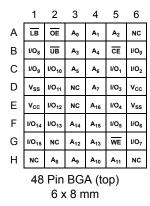
#### Features

- Single Wide Power Supply Range 1.65 to 2.2 Volts
- Very low standby current 0.5µA at 1.8V (Typical)
- Very low operating current 1.4mA at 1.8V and 1µs (Typical)
- Very low Page Mode operating current 0.5mA at 1.8V and 1µs (Typical)
- Simple memory control Single Chip Enable (CE) Byte control for independent byte operation Output Enable (OE) for memory expansion
- Low voltage data retention Vcc = 1.2V
- Very fast output enable access time 30ns  $\overline{OE}$  access time
- Automatic power down to standby mode
- TTL compatible three-state output driver
- Compact space saving BGA package

Part Number	Package Type	Operating Temperature	Power Supply (Vcc)	Speed	Standby Current (I <sub>SB</sub> ), Max	Operating Current (Icc), Max
N02L6181AB	48 - BGA	-40 <sup>o</sup> C to +85 <sup>o</sup> C	1651/ 221/	70 and 85ns	10 uA	3 mA @ 1MHz
N02L6181AB2	Green 48-BGA	-40°C to +85°C	1.000 - 2.20	@ 1.65V	το μΑ	



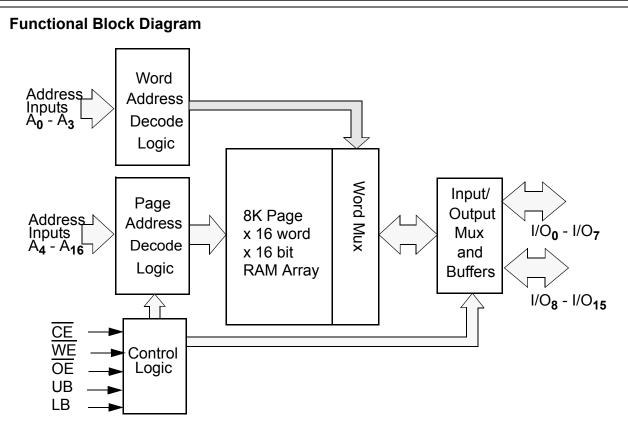
#### **Pin Configurations**



#### **Pin Descriptions**

Pin Name	Pin Function		
A <sub>0</sub> -A <sub>16</sub>	Address Inputs		
WE	Write Enable Input		
CE	Chip Enable Input		
OE	Output Enable Input		
LB	Lower Byte Enable Input		
UB	Upper Byte Enable Input		
I/O <sub>0</sub> -I/O <sub>15</sub>	Data Inputs/Outputs		
NC	Not Connected		
V <sub>CC</sub>	Power		
V <sub>SS</sub>	Ground		





#### **Functional Description**

CE	WE	OE	UB	LB	I/O <sub>0</sub> - I/O <sub>15</sub> <sup>1</sup> MODE		POWER
Н	Х	Х	Х	Х	High Z	Standby <sup>2</sup>	Standby
L	Х	Х	Н	Н	High Z Standby <sup>2</sup>		Standby
L	L	X <sup>3</sup>	L <sup>1</sup>	L <sup>1</sup>	Data In	Write <sup>3</sup>	Active
L	Н	L	L <sup>1</sup>	L <sup>1</sup>	Data Out Read		Active
L	Н	Н	L <sup>1</sup>	L <sup>1</sup>	High Z Active		Active

1. When  $\overline{\text{UB}}$  and  $\overline{\text{LB}}$  are in select mode (low), I/O<sub>0</sub> - I/O<sub>15</sub> are affected as shown. When  $\overline{\text{LB}}$  only is in the select mode only I/O<sub>0</sub> - I/O<sub>7</sub> are affected as shown. When  $\overline{\text{UB}}$  is in the select mode only I/O<sub>8</sub> - I/O<sub>15</sub> are affected as shown.

2. When the device is in standby mode, control inputs (WE, OE, UB, and LB), address inputs and data input/outputs are internally isolated from any external influence and disabled from exerting any influence externally.

3. When  $\overline{\text{WE}}$  is invoked, the  $\overline{\text{OE}}$  input is internally disabled and has no effect on the circuit.

### Capacitance<sup>1</sup>

Item	Symbol	Test Condition	Min	Мах	Unit
Input Capacitance	C <sub>IN</sub>	V <sub>IN</sub> = 0V, f = 1 MHz, T <sub>A</sub> = 25°C		8	pF
I/O Capacitance	C <sub>I/O</sub>	V <sub>IN</sub> = 0V, f = 1 MHz, T <sub>A</sub> = 25°C		8	pF

1. These parameters are verified in device characterization and are not 100% tested



#### Absolute Maximum Ratings<sup>1</sup>

Item	Symbol	Rating	Unit
Voltage on any pin relative to $V_{SS}$	V <sub>IN,OUT</sub>	-0.3 to V <sub>CC</sub> +0.3	V
Voltage on $V_{CC}$ Supply Relative to $V_{SS}$	V <sub>CC</sub>	-0.3 to 3.0	V
Power Dissipation	PD	500	mW
Storage Temperature	T <sub>STG</sub>	-40 to 125	°C
Operating Temperature	T <sub>A</sub>	-40 to +85	°C
Soldering Temperature and Time	T <sub>SOLDER</sub>	240 <sup>o</sup> C, 10sec(Lead only)	°C

 Stresses greater than those listed above may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operating section of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.

#### **Operating Characteristics (Over Specified Temperature Range)**

Item	Symbol	Test Conditions	Min.	Typ <sup>1</sup>	Мах	Unit
Supply Voltage	V <sub>CC</sub>		1.65	1.8	2.2	V
Data Retention Voltage	$V_{DR}$	Chip Disabled <sup>2</sup>	1.2		2.2	V
Input High Voltage	V <sub>IH</sub>		0.7Vcc		V <sub>CC</sub> +0.3	V
Input Low Voltage	V <sub>IL</sub>		-0.3		0.3Vcc	V
Output High Voltage	V <sub>OH</sub>	I <sub>OH</sub> = 0.2mA	V <sub>CC</sub> -0.2			V
Output Low Voltage	V <sub>OL</sub>	I <sub>OL</sub> = -0.2mA			0.3	V
Input Leakage Current	Ι <sub>LI</sub>	$V_{IN}$ = 0 to $V_{CC}$			0.5	μA
Output Leakage Current	I <sub>LO</sub>	$\overline{OE} = V_{IH}$ or Chip Disabled			0.5	μA
Read/Write Operating Supply Current @ 1 µs Cycle Time <sup>2</sup>	I <sub>CC1</sub>	V <sub>CC</sub> =2.2 V, V <sub>IN</sub> =V <sub>IH</sub> or V <sub>IL</sub> Chip Enabled, I <sub>OUT</sub> = 0		1.4	3.0	mA
Read/Write Operating Supply Current @ 70 ns Cycle Time <sup>2</sup>	I <sub>CC2</sub>	$V_{CC}$ =2.2 V, $V_{IN}$ = $V_{IH}$ or $V_{IL}$ Chip Enabled, $I_{OUT}$ = 0		8.0	17.0	mA
Page Mode Operating Supply Current @ 70ns Cycle Time <sup>2</sup> (Refer to Power Savings with Page Mode Operation diagram)	I <sub>CC3</sub>	V <sub>CC</sub> =2.2V, V <sub>IN</sub> =V <sub>IH</sub> or V <sub>IL</sub> Chip Enabled, I <sub>OUT</sub> = 0		2.0	4.0	mA
Read/Write Quiescent Operating Sup- ply Current <sup>3</sup>	I <sub>CC4</sub>	$V_{CC}$ =2.2V, $V_{IN}$ = $V_{IH}$ or $V_{IL}$ Chip Enabled, $I_{OUT}$ = 0, f = 0			0.1	mA
Maximum Standby Current <sup>3</sup>	I <sub>SB1</sub>	$V_{IN} = V_{CC} \text{ or } 0V$ Chip Disabled $t_A = 85^{\circ}C$ , VCC = 2.2 V		0.5	10.0	μA
Maximum Data Retention Current <sup>3</sup>	I <sub>DR</sub>	$V_{CC}$ = 1.2V, $V_{IN}$ = $V_{CC}$ or 0 Chip Disabled, $t_A$ = 85°C			5.0	μA

1. Typical values are measured at Vcc=Vcc Typ.,  $T_A = 25^\circ C$  and are not 100% tested.

2. This parameter is specified with the outputs disabled to avoid external loading effects. The user must add current required to drive output capacitance expected in the actual system.

 This device assumes a standby mode if the chip is disabled (CE high). In order to achieve low standby current all inputs must be within 0.2 volts of either VCC or VSS



Power Savir	ower Savings with Page Mode Operation (WE = V <sub>IH</sub> )					
Page Addre	ess (A4 - A16 ) Open page	X				
Word Addre	ress (A0 - A3) X Word 1 X Word 2 Word 16					
CE						
ŌĒ						
LB, UB						

Note: Page mode operation is a method of addressing the SRAM to save operating current. The internal organization of the SRAM is optimized to allow this unique operating mode to be used as a valuable power saving feature.

The only thing that needs to be done is to address the SRAM in a manner that the internal page is left open and 16-bit words of data are read from the open page. By treating addresses A0-A3 as the least significant bits and addressing the 16 words within the open page, power is reduced to the page mode value which is considerably lower than standard operating currents for low power SRAMs.



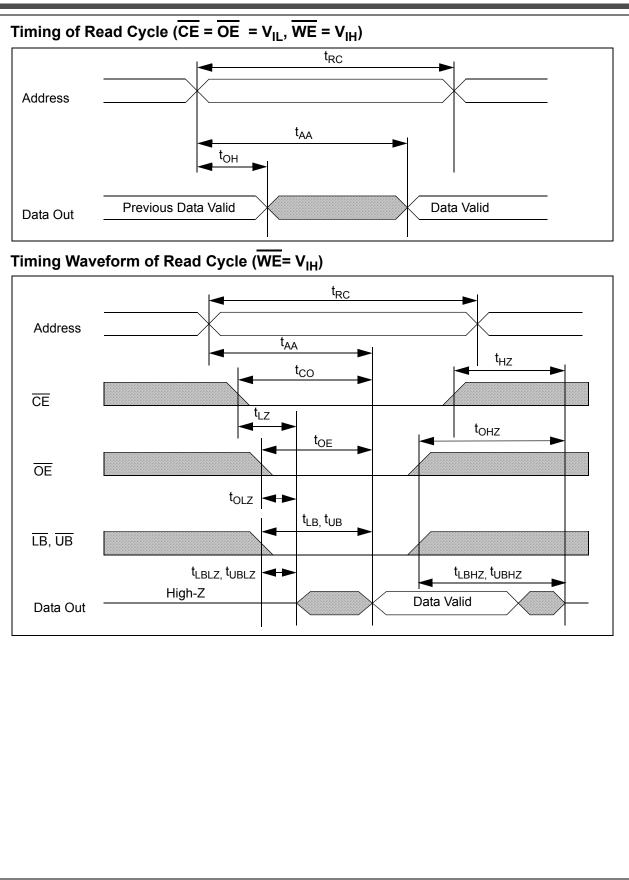
#### **Timing Test Conditions**

Item	
Input Pulse Level	0.1V <sub>CC</sub> to 0.9 V <sub>CC</sub>
Input Rise and Fall Time	5ns
Input and Output Timing Reference Levels	0.5 V <sub>CC</sub>
Output Load	CL = 30pF
Power Supply Voltage	1.65 - 2.2V
Operating Temperature	-40 to +85 <sup>o</sup> C

#### Timing

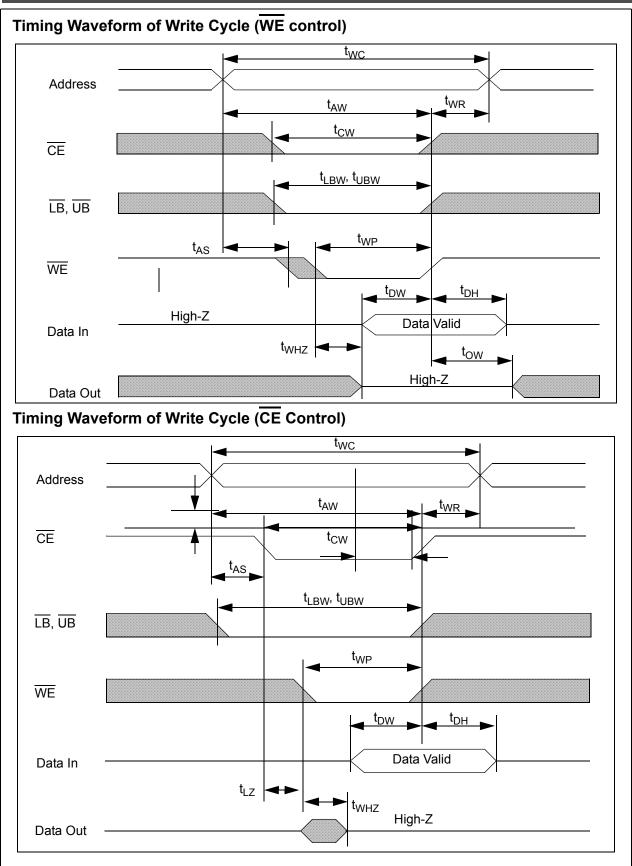
	Cumhal	85	ins	70ns		Unito	
Item	Symbol	Min.	Max.	Min.	Max.	Units	
Read Cycle Time	t <sub>RC</sub>	85		70		ns	
Address Access Time	t <sub>AA</sub>		85		70	ns	
Chip Enable to Valid Output	t <sub>co</sub>		85		70	ns	
Output Enable to Valid Output	t <sub>OE</sub>		30		25	ns	
Byte Select to Valid Output	t <sub>LB</sub> , t <sub>UB</sub>		85		70	ns	
Chip Enable to Low-Z output	t <sub>LZ</sub>	10		10		ns	
Output Enable to Low-Z Output	t <sub>OLZ</sub>	5		5		ns	
Byte Select to Low-Z Output	t <sub>LBZ</sub> , t <sub>UBZ</sub>	10		10		ns	
Chip Disable to High-Z Output	t <sub>HZ</sub>		30		25	ns	
Output Disable to High-Z Output	t <sub>OHZ</sub>		30		25	ns	
Byte Select Disable to High-Z Output	t <sub>LBHZ</sub> , t <sub>UBHZ</sub>		30		25	ns	
Output Hold from Address Change	t <sub>OH</sub>	5		5		ns	
Write Cycle Time	t <sub>WC</sub>	85		70		ns	
Chip Enable to End of Write	t <sub>CW</sub>	50		40		ns	
Address Valid to End of Write	t <sub>AW</sub>	50		40		ns	
Byte Select to End of Write	t <sub>LBW</sub> , t <sub>UBW</sub>	50		40		ns	
Write Pulse Width	t <sub>WP</sub>	50		40		ns	
Address Setup Time	t <sub>AS</sub>	0		0		ns	
Write Recovery Time	t <sub>WR</sub>	0		0		ns	
Write to High-Z Output	t <sub>WHZ</sub>		25		20	ns	
Data to Write Time Overlap	t <sub>DW</sub>	40		40		ns	
Data Hold from Write Time	t <sub>DH</sub>	0		0		ns	
End Write to Low-Z Output	t <sub>ow</sub>	10		10		ns	



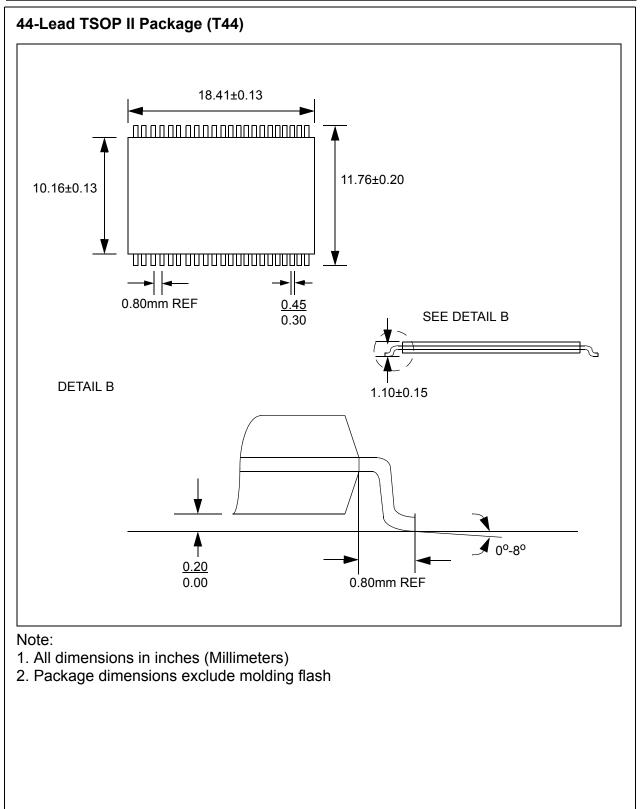


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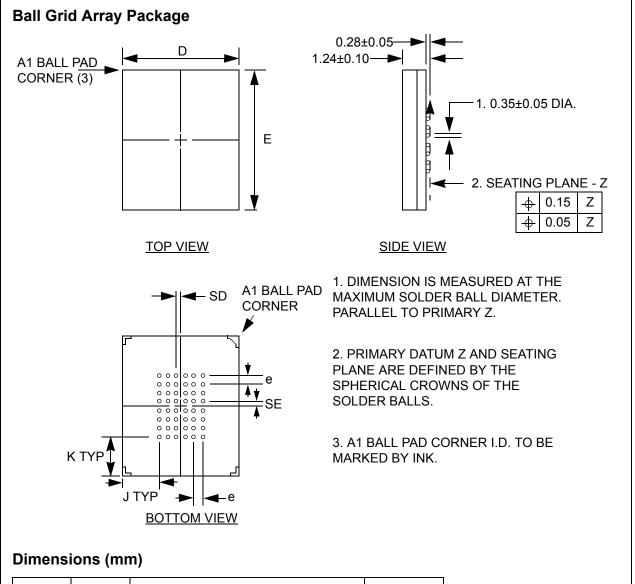






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## N02L6181A



D	Е		BALL MATRIX			
D	L	SD	SE	J	К	TYPE
6±0.10	8±0.10	0.375	0.375	1.125	1.375	FULL



#### **Ordering Information**

Part Number	Package	Shipping Method	Speed
N02L6181AB7I	Leaded 48-BGA	Tray	70ns
N02L6181AB27I	Green 48-BGA (RoHS Compliant)	Tray	70ns
N02L6181AB8I	Leaded 48-BGA	Tray	85ns
N02L6181AB28I	Green 48-BGA (RoHS Compliant)	Tray	85ns
N02L6181AB7IT	Leaded 48-BGA	Tape & Reel	70ns
N02L6181AB27IT	Green 48-BGA (RoHS Compliant)	Tape & Reel	70ns
N02L6181AB8IT	Leaded 48-BGA	Tape & Reel	85ns
N02L6181AB28IT	Green 48-BGA (RoHS Compliant)	Tape & Reel	85ns

#### **Revision History**

Revision #	Date	Change Description		
A	Apr. 2003	Initial Release		
В	Nov. 2005	Added TSOP II Green Pkg., Green Pkg. Part # and RoHS Compliant		
С	September 2006	Converted to AMI Semiconductor		
4	July 2008	Converted to ON Semiconductor and new part numbers		

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